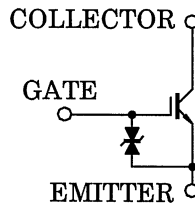


GT8G103

STROBE FLASH APPLICATIONS

- 3rd Generation
- Enhancement-Mode
- Low Saturation Voltage: $V_{CE(sat)} = 8\text{ V (Max.) (@}I_C = 150\text{ A)}$
- 4.5 V Gate Drive



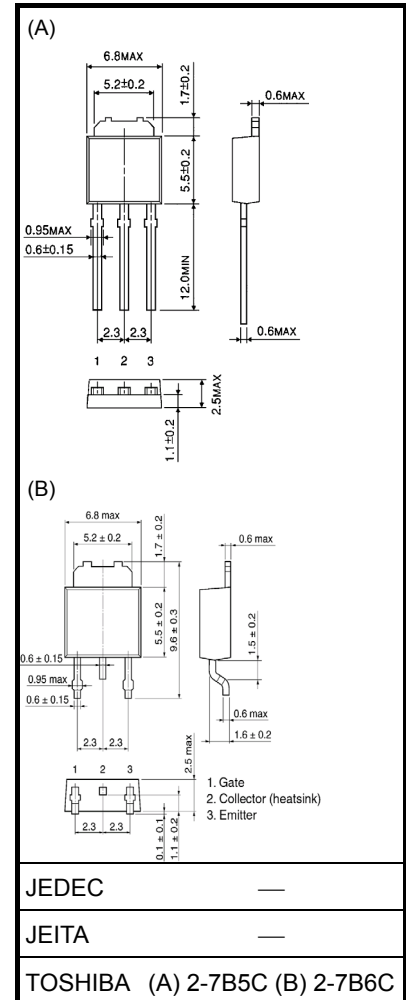
Unit: mm

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V_{CES}	400	V
Gate-Emitter Voltage	DC	V_{GES}	±6 V
	Pulse	V_{GES}	±8 V
Collector Current	DC	I_C	8 A
	1 ms	I_{CP}	150 A
Collector Power Dissipation	Ta = 25°C	P_C	1.3 W
	Tc = 25°C	P_C	20 W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



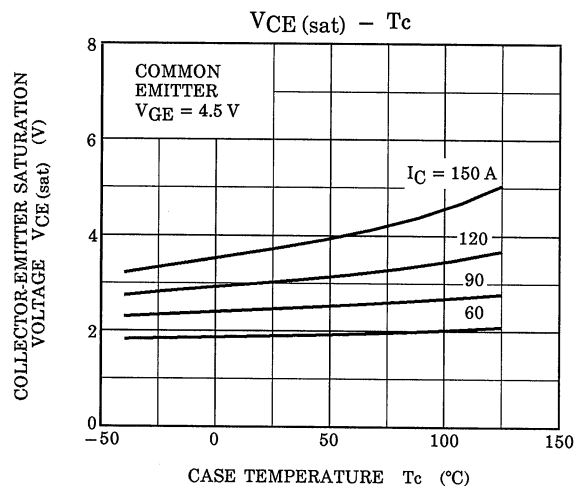
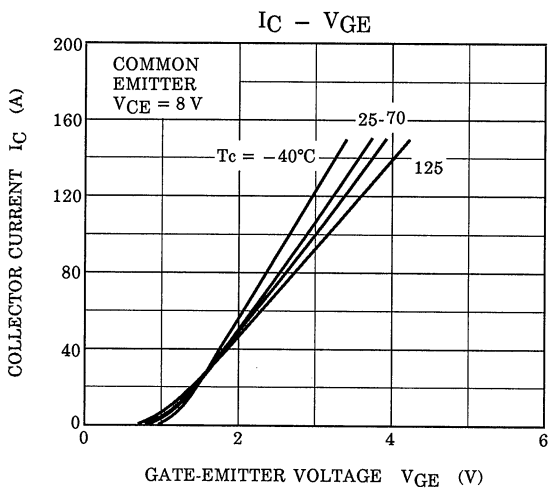
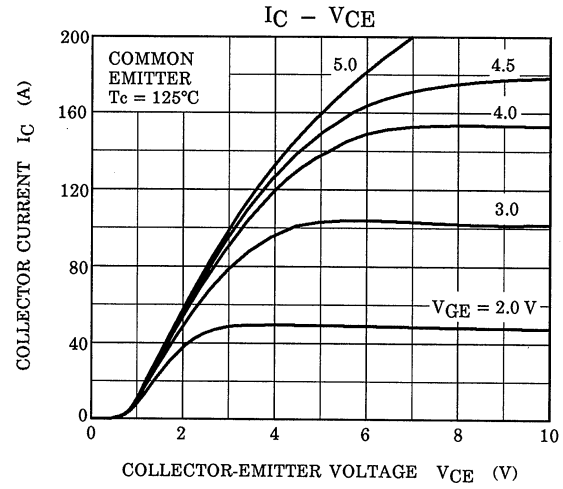
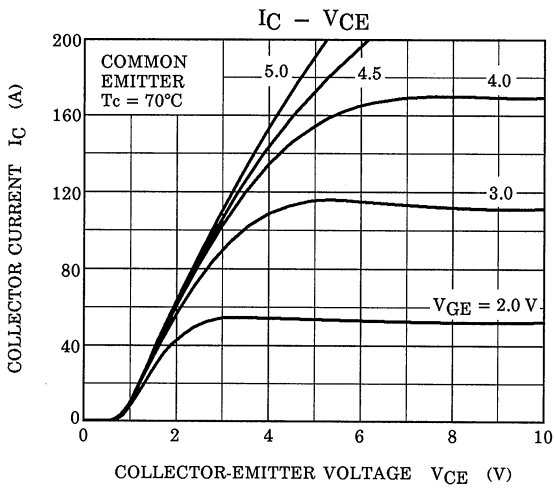
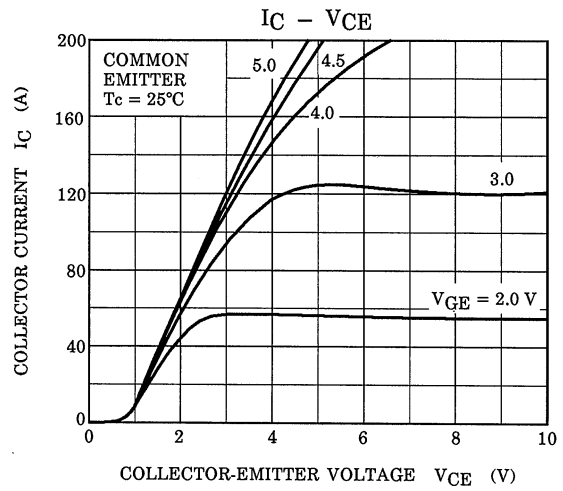
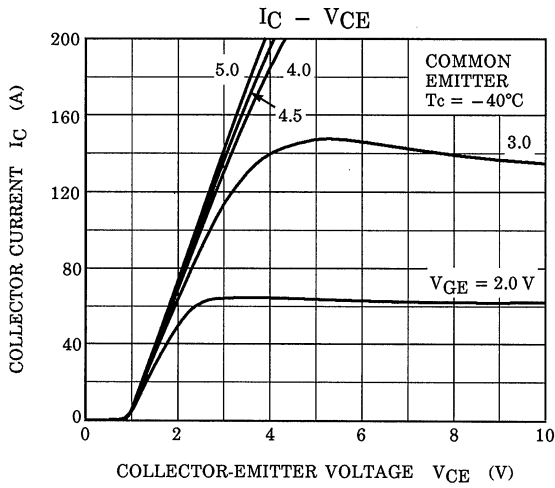
JEDEC	—
JEITA	—
TOSHIBA	(A) 2-7B5C (B) 2-7B6C

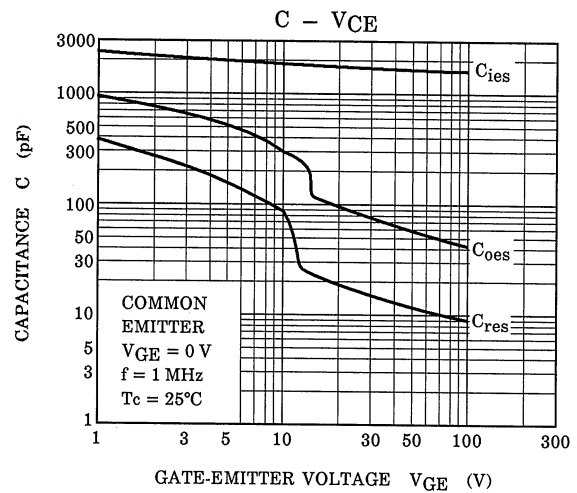
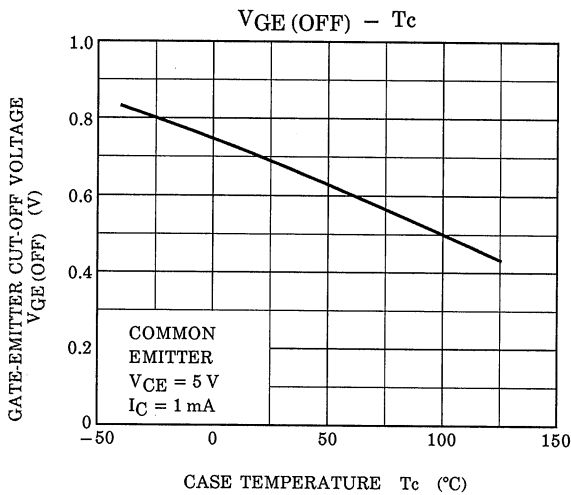
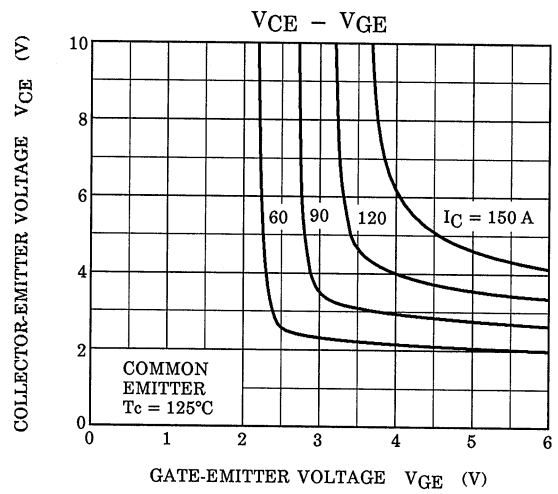
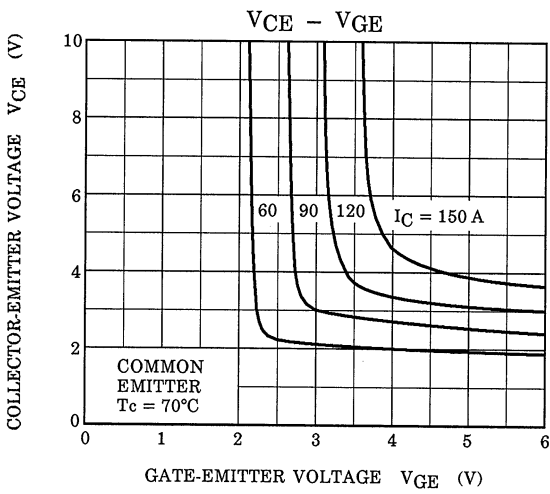
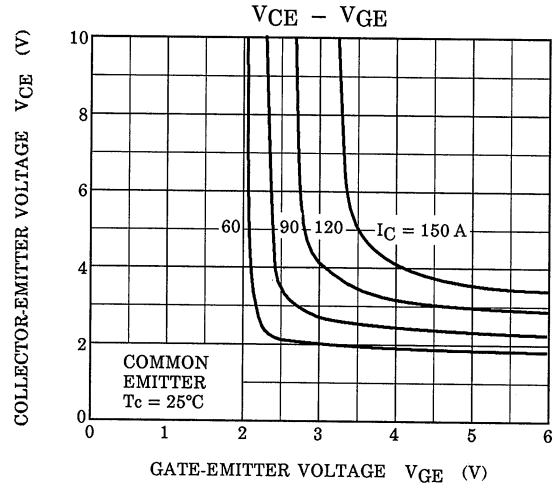
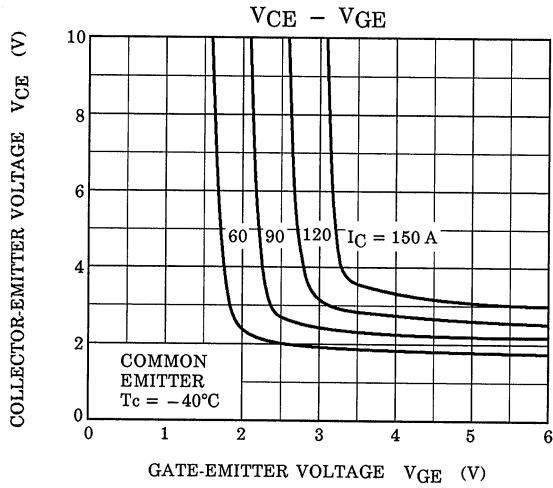
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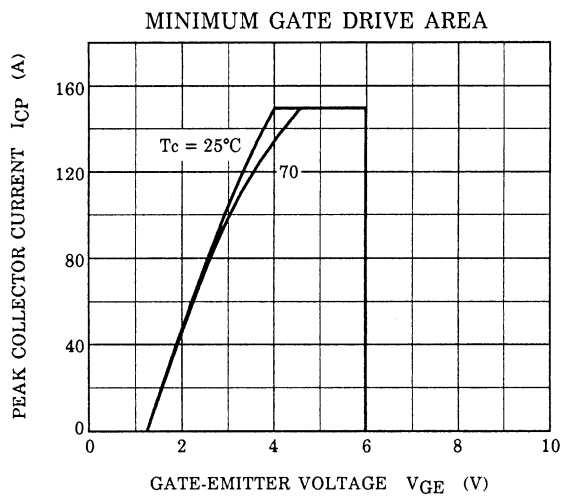
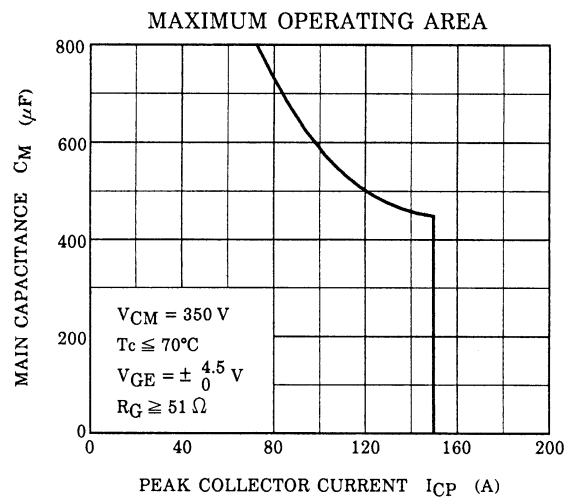
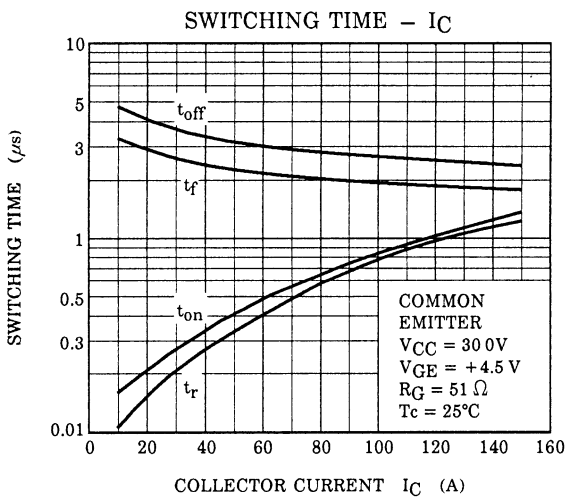
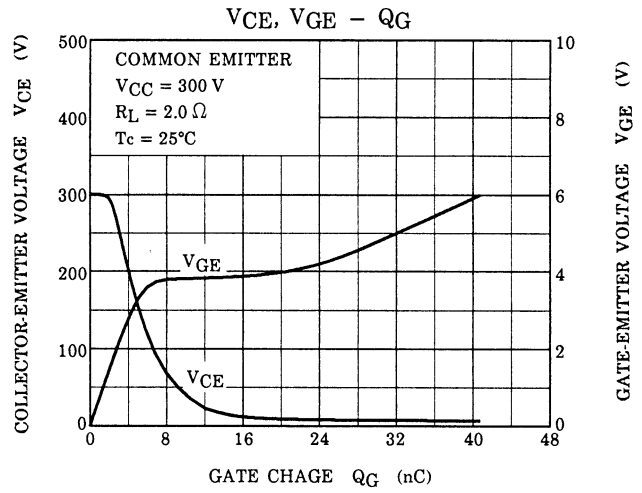
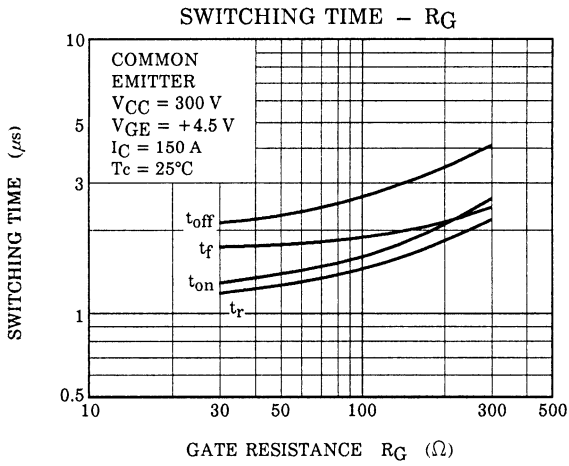
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Gate Leakage Current	I_{GES}	$V_{GE} = 6\text{ V}, V_{CE} = 0$	—	—	10	μA
Collector Cut-off Current	I_{CES}	$V_{CE} = 400\text{ V}, V_{GE} = 0$	—	—	10	μA
Gate-Emitter Cut-off Voltage	$V_{GE(OFF)}$	$I_C = 1\text{ mA}, V_{CE} = 5\text{ V}$	0.5	—	1.2	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 150\text{ A}, V_{GE} = 4.5\text{ V (Pulsed)}$	—	5	8	V
Input Capacitance	C_{ies}	$V_{CE} = 10\text{ V}, V_{GE} = 0, f = 1\text{ MHz}$	—	1900	—	pF
Switching Time	Rise Time		—	1.2	—	μs
	Turn-on Time		—	1.4	—	
	Fall Time		—	1.8	—	
	Turn-off Time		—	2.4	—	
Thermal Resistance	$R_{th(j-c)}$	—	—	—	6.25	°C / W

These devices are MOS type. Users should follow proper ESD Handling Procedures. Operating condition of turn-off dv / dt should be lower than 400 V / μs.







RESTRICTIONS ON PRODUCT USE

20070701-EN

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